Measurements of valley splitting in novel Si/SiGe heterostructures\textsuperscript{1} SAMUEL F. NEYENS\textsuperscript{*}, RYAN H. FOOTE\textsuperscript{*}, T. J. KNAPP\textsuperscript{*}, BRANDUR THORGRIMSSON\textsuperscript{*}, L. M. K. VANDERSYPEN\textsuperscript{†}, PAYAM AMIN\textsuperscript{‡}, ANTONIO RODOLPH B. MEI\textsuperscript{‡}, NICOLE K. THOMAS\textsuperscript{†}, JAMES S. CLARKE\textsuperscript{†}, D. E. SAVAGE\textsuperscript{*}, M. G. LAGALLY\textsuperscript{*}, MARK FRIESEN\textsuperscript{‡}, S. N. COPPERSMITH\textsuperscript{*}, M. A. ERIKSSON\textsuperscript{†}, University of Wisconsin-Madison, \textsuperscript{†}Delft University of Technology, \textsuperscript{‡}Intel Corp. — Achieving an appropriate valley splitting is important for making quantum dot qubits in Si/SiGe heterostructures. We measure valley splittings in novel heterostructures grown with an extra layer of Ge, \textasciitilde{}5 monolayers in thickness, between the Si well and the SiGe barrier. For one of these extra-Ge heterostructures, the CVD growth was interrupted between the Si well and the Ge layer to achieve a more abrupt change in composition. The other extra-Ge heterostructure was made with a continuous growth process. Using Hall bar devices on both of these extra-Ge samples as well as one standard sample with no extra Ge, we measure activation energies for valley splittings in the first and second Landau levels. For the $\nu = 3$ valley splitting, we find the abrupt, extra-Ge sample has consistently the highest valley splitting across three different carrier densities. For these densities, the valley splitting in the abrupt, extra-Ge sample is \textasciitilde{}50\% higher than that of the standard sample.

\textsuperscript{1}This work was supported in part by ARO (W911NF-12-0607) and NSF (DMR-1206915). Development and maintenance of the growth facilities used for fabricating samples is supported by DOE (DE-FG02-03ER46028).

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Date submitted: 11 Nov 2016

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